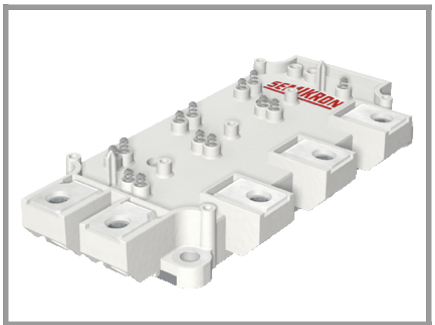


SEMiX®13

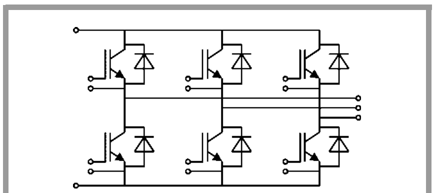
Trench IGBT Modules

SEMiX101GD12E4s

Features
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

Typical Applications
- AC inverter drives
- UPS
- Electronic Welding

Remarks
- Case temperature limited to T_C=125°C max.
- Product reliability results are valid for T_j=150°C



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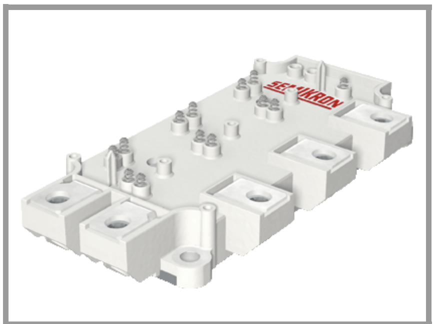
Absolute Maximum Ratings				
Symbol	**Conditions**		**Values**	**Unit**
IGBT				
V_{CES}			1200	V
I_C	T_j = 175 °C	T_c = 25 °C	160	A
		T_c = 80 °C	123	A
I_{Cnom}			100	A
I_{CRM}	$I_{CRM} = 3xI_{Cnom}$		300	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 800 V $V_{GE} \leq 20$ V $V_{CES} \leq 1200$ V	T_j = 150 °C	10	µs
T_j			-40 ... 175	°C
Inverse diode				
I_F	T_j = 175 °C	T_c = 25 °C	121	A
		T_c = 80 °C	91	A
I_{Fnom}			100	A
I_{FRM}	$I_{FRM} = 3xI_{Fnom}$		300	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 25 °C		550	A
T_j			-40 ... 175	°C
Module				
$I_{t(RMS)}$			600	A
T_{stg}			-40 ... 125	°C
V_{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
IGBT						
$V_{CE(sat)}$	I_C = 100 A V_{GE} = 15 V chiplevel	T_j = 25 °C		1.8	2.05	V
		T_j = 150 °C		2.2	2.4	V
V_{CE0}		T_j = 25 °C		0.8	0.9	V
		T_j = 150 °C		0.7	0.8	V
r_{CE}	V_{GE} = 15 V	T_j = 25 °C		10.0	11.5	mΩ
		T_j = 150 °C		15.0	16.0	mΩ
$V_{GE(th)}$	V_{GE}=V_{CE}, I_C = 3.8 mA		5	5.8	6.5	V
I_{CES}	V_{GE} = 0 V V_{CE} = 1200 V	T_j = 25 °C		0.1	0.3	mA
		T_j = 150 °C				mA
C_{ies}	V_{CE} = 25 V V_{GE} = 0 V	f = 1 MHz		6.2		nF
C_{oes}		f = 1 MHz		0.41		nF
C_{res}		f = 1 MHz		0.34		nF
Q_G	V_{GE} = - 8 V...+ 15 V			565		nC
R_{Gint}	T_j = 25 °C			7.50		Ω
$t_{d(on)}$	V_{CC} = 600 V I_C = 100 A $R_{G\,on}$ = 1 Ω $R_{G\,off}$ = 1 Ω di/dt_{on} = 3100 A/µs di/dt_{off} = 1200 A/µs	T_j = 150 °C		187		ns
t_r		T_j = 150 °C		35		ns
E_{on}		T_j = 150 °C		10.8		mJ
$t_{d(off)}$		T_j = 150 °C		467		ns
t_f		T_j = 150 °C		94		ns
E_{off}		T_j = 150 °C		13.3		mJ
$R_{th(j-c)}$	per IGBT				0.27	K/W



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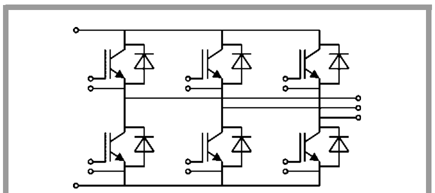

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Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
Inverse diode						
$V_F = V_{EC}$	I_F = 100 A V_{GE} = 0 V chip	T_j = 25 °C		2.2	2.52	V
		T_j = 150 °C		2.1	2.5	V
V_{F0}		T_j = 25 °C	1.1	1.3	1.5	V
		T_j = 150 °C	0.7	0.9	1.1	V
r_F		T_j = 25 °C	8.0	9.0	10.2	mΩ
		T_j = 150 °C	10.5	12.5	13.7	mΩ
I_{RRM}	I_F = 100 A di/dt_{off} = 3000 A/µs V_{GE} = -15 V V_{CC} = 600 V	T_j = 150 °C		95		A
Q_{rr}		T_j = 150 °C		16		µC
E_{rr}		T_j = 150 °C		6.5		mJ
$R_{th(j-c)}$	per diode				0.48	K/W
Module						
L_{CE}				20		nH
$R_{CC'+EE'}$	res., terminal-chip	T_C = 25 °C		0.7		mΩ
		T_C = 125 °C		1		mΩ
$R_{th(c-s)}$	per module			0.04		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t		to terminals (M6)	2.5		5	Nm
						Nm
w					350	g
Temperatur Sensor						
R_{100}	T_c=100°C (R_{25}=5 kΩ)			493 ± 5%		Ω
$B_{100/125}$	$R_{(T)}=R_{100}exp[B_{100/125}(1/T-1/T_{100})]$; T[K];			3550 ±2%		K

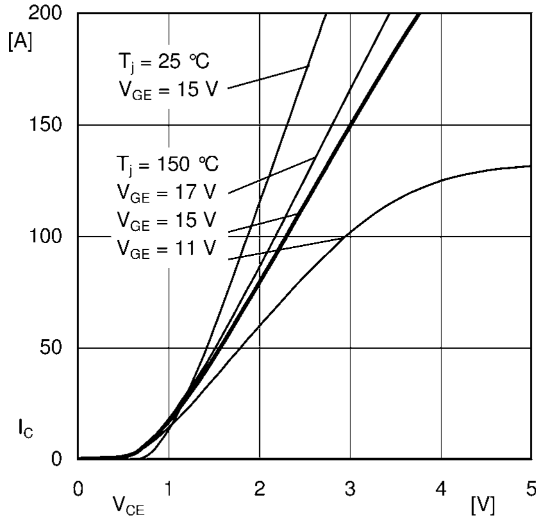


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

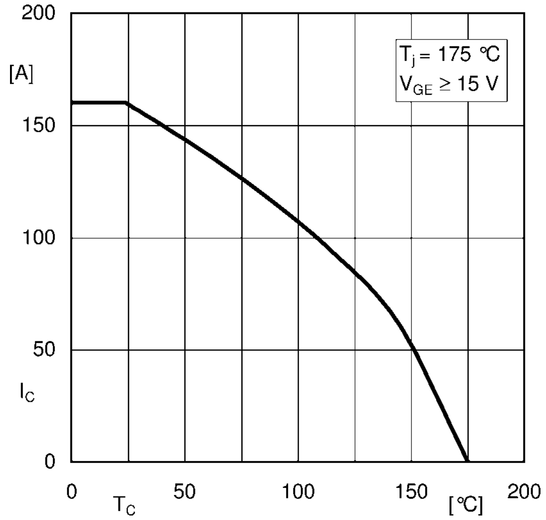


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

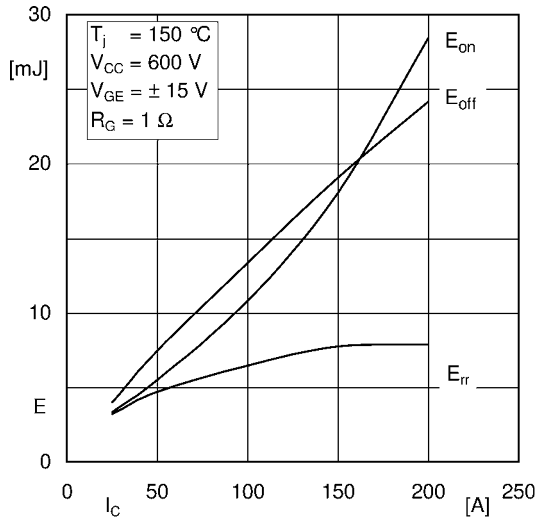


Fig. 3: Typ. turn-on /-off energy = f (I_C)

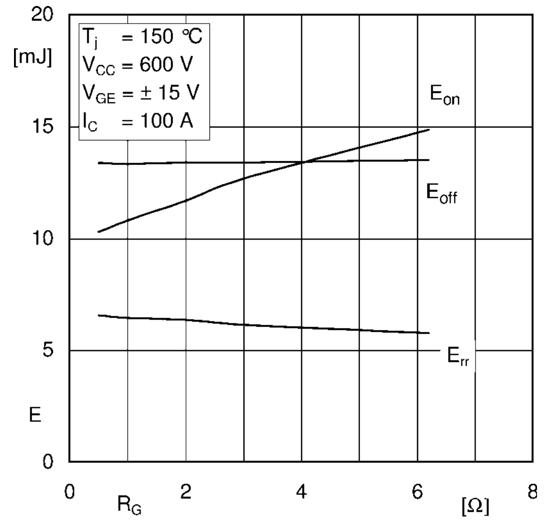


Fig. 4: Typ. turn-on /-off energy = f (R_G)

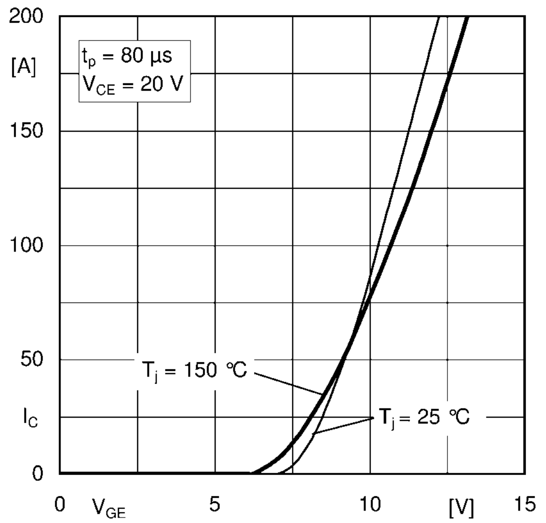


Fig. 5: Typ. transfer characteristic

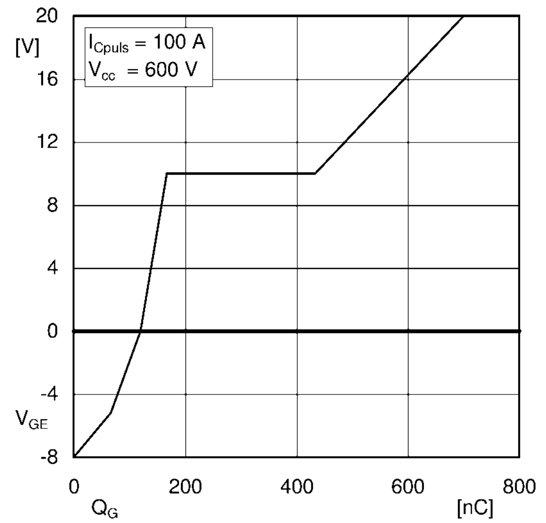


Fig. 6: Typ. gate charge characteristic

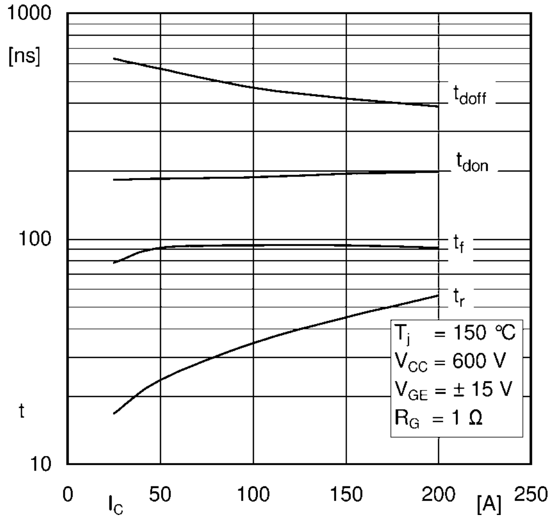


Fig. 7: Typ. switching times vs. I_C

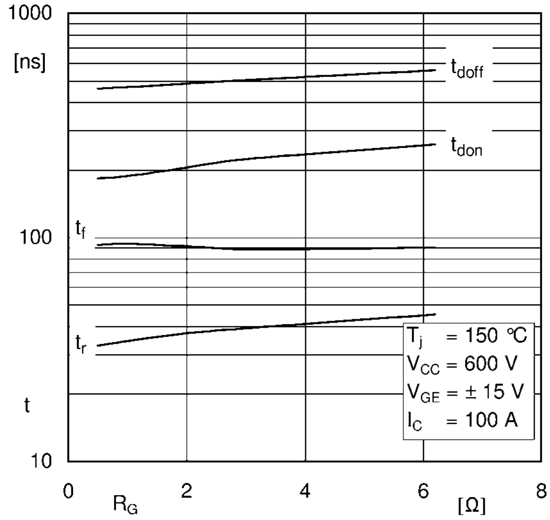


Fig. 8: Typ. switching times vs. gate resistor R_G

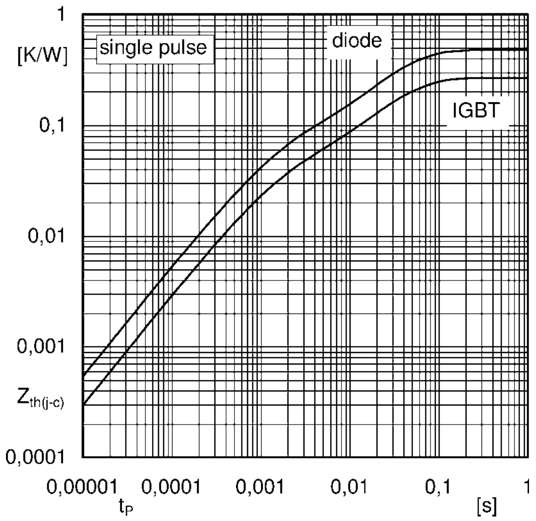


Fig. 9: Typ. transient thermal impedance

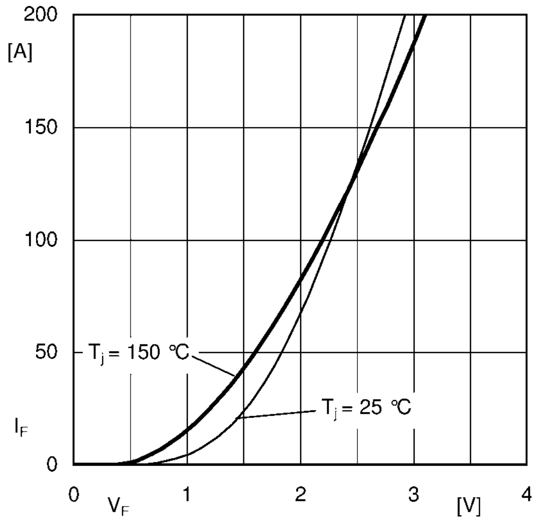


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

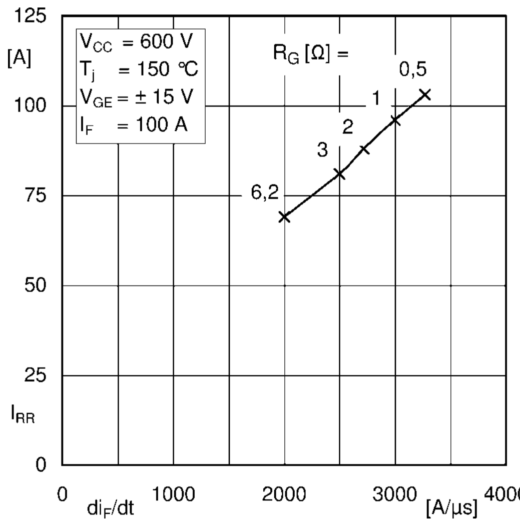


Fig. 11: Typ. CAL diode peak reverse recovery current

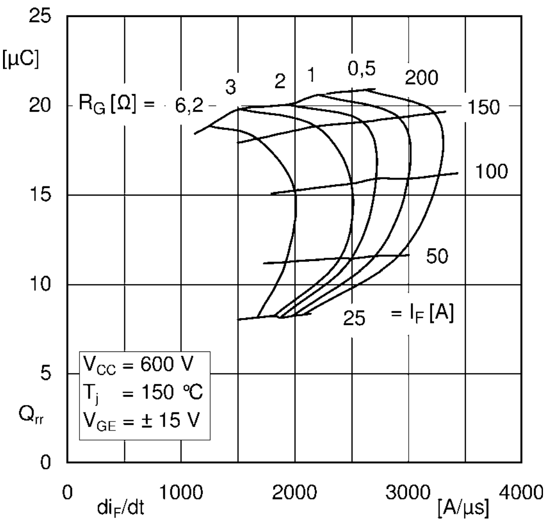
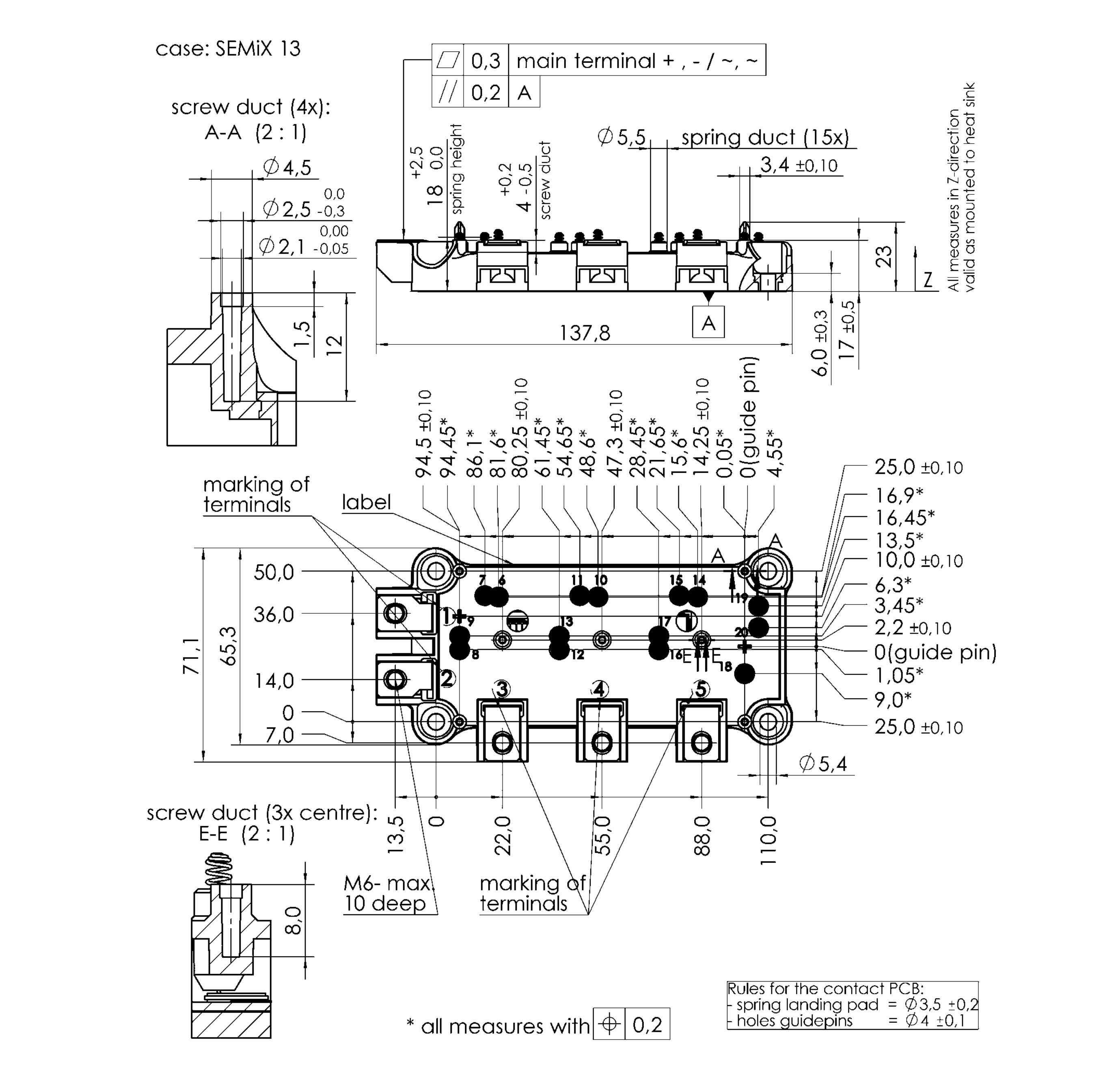


Fig. 12: Typ. CAL diode recovery charge



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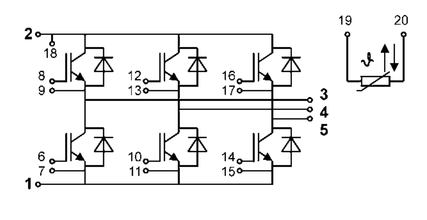

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

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